## I. PHYSICAL ELECTRONICS

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## A. ELECTRON EMISSION PROBLEMS

1. Effect of a Magnetic Field and of a Unidirectional Heating Current on Thermionic Emission from Molybdenum

The chief purpose of this research — investigation of the effect of a magnetic field on thermionic-emission current — was described in the Quarterly Progress Report of January 15, 1957, page 2, together with a description of the tube design and a discussion of the background of the experiment. We shall also study another effect, which can be easily investigated with the same tube structure. This concerns the possibility of changes in the surface structure of the filament as a result of sustained dc heating. We believe that the application of dc heating over a period of time will cause a shifting or migration of the surface atoms, and thus a change in the exposed crystal structure. This change would probably result in a preferred direction of emission; that is, the emission from the two sides of the ribbon filament would be unequal.

This study will require measurement of the emission current to each of the four collector plates as a function of the length of time of dc treatment, and as a function of the magnitude and direction of the heating current. Until the effect of direct current is tested, all heating will be by alternating current. Since the emission is a highly sensitive function of temperature, and therefore of filament current, a steady heater voltage is essential. Effort is now being devoted to perfecting an electronic ac voltage-regulator circuit which is expected to reduce fluctuations in the line voltage to 5 per cent of their initial value (1). For dc heating, the regulator developed by H. Shelton, of this laboratory, will be employed (2).

J. Greenburg

#### References

- 1. The basic circuit is given in L. D. Harris, An electronic a.c. voltage regulator, Bulletin No. 28, Utah Engineering Experiment Station, University of Utah, June 1945.
- 2. H. Shelton, Ph.D. Thesis, Department of Physics, M.I.T., May 1956, pp. 32-34.

## B. PHYSICAL ELECTRONICS IN THE SOLID STATE

#### 1. Characteristics of Junctions in Germanium

Measurement of the characteristics of germanium alloy - junction rectifiers at low voltages reported in the Quarterly Progress Report of April 15, 1957, page 7, continues,

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with the measurement of the barrier height and its apparent temperature dependence in a third junction, sample AB3. This junction is constructed from 0.6 ohm-cm germanium, in the same manner in which the previous junctions were constructed. If we assume that the height B of the potential barrier at the junction is  $B = B_0 + aV_T$ , then the constants for this rectifier are  $B_0 = 0.557$  volt, a = 5.24.

Present work is an attempt to predict the usual rectifying characteristics from the low-voltage measurements of  $B_0$  and a. The measurements on sample JA357 indicate that this can, indeed, be done, the current density j through the junction being given by the relation

$$j = A'V_T^2 \exp(-B_0/V_T - a) \left[\exp(-V_B/V_T) - 1\right]$$

where  $A' = 4\pi mq^3/h^3 = 1.619 \times 10^{14}$  amp/meter<sup>2</sup> volts<sup>2</sup>,  $V_T = kT/q = T/11,606$  volts, and  $V_B$  is the voltage across the junction. (Notice that the previously reported value of A' was in error.) Sample AB3, however, does not show this behavior, since the current in the reverse direction does not reach a saturation value. This sample was previously damaged by pressure on the indium contact, and probably has leakage paths around the junction; it is also quite unstable at high voltages.

Samples of different types, such as point-contact and grown-junction rectifiers, are being obtained so that data on them can be compiled. Because the present measurements use a potentiometer for voltage measurements, they take a great amount of time, and the possibility of using a chopper amplifier instead of the potentiometer is being investigated. J. F. Campbell, Jr.

## 2. Surface States on Semiconductors

A tube was constructed for measuring the changes in the photoconductivity and the contact potential of a germanium sample simultaneously. However, it was impossible to take accurate measurements because of stray voltages that originated in the tube. These voltages consisted partly of random noise, but mostly of microphonics. We also found that the contact resistance of the germanium sample was extremely high, approximately two orders of magnitude higher than that of the sample itself. The tube was torn down and rebuilt several times, but it was still plagued with cracks caused by strains in the glass. We originally planned not to bake the sealed tube so that the sample would not be heated and drive off adsorbed compounds that might give rise to traps (in Gebbie's experiment (1), of which this study is a continuation, the germanium samples were mounted without heating in a demountable system). After the frequent occurrence of cracks we decided to bake the tube with the germanium in it. This helped to relieve strains in the glass and improved the vacuum in the tube  $(8 \times 10^{-10} \text{ mm Hg} \text{ on the pump})$  but gave rise to slight deformations in the tube during baking periods,

which caused short circuits in the tube. The ends of a new germanium sample were plated with gold, and the contact resistance of the ends was subsequently found to be small in comparison with that of the sample. The random noise was also reduced. The main assembly in the tube and the electron-deflector plate were both welded to additional press wires to achieve greater rigidity in the mounting. This considerably reduced the microphonics, and led to the conclusion that they were caused by a Kelvin effect between the vibrating metal parts in the tube. At one time a crude experimental photoconductivity run was taken, and the response was approximately linear with light intensity with no saturating component (as in Gebbie's experiment) present. An oscilloscope trace showed no evidence of slow decay of photoconductivity when the light was cut off, and therefore no evidence of trapping either. We hope to create trapping centers by bombarding the surface with a Tesla coil in an oxygen ambient.

After a few more cracks and short circuits had developed, we decided to redesign the tube envelope so that all of the parts whose alignment is critical would be mounted on wires of a single common press (instead of on wires of different single-lead presses). Such a tube was built, and we found that no more short circuits developed. The electron accelerating mechanism was tried, and an electron current of approximately  $10^{-7}$  amp was collected at the germanium sample. This is small compared with the total emission current of 50 ma, but it does prove the workability of the system. The electron deflector potential was the same as that of the center of the emitting filament.

The sample is etched with CP-4 and rinsed with high-purity water before every installation in the tube. The plated ends are protected during the etching by paraffin wax which is later dissolved in trichlorethylene. Argon is blown into the tube during the sealing process to reduce oxidation of the metal parts.

E. Ahilea

#### References

 H. A. Gebbie and E. Ahilea, Surface electronics on semiconductors, Quarterly Progress Report, Research Laboratory of Electronics, M.I.T., July 15, 1955, pp. 3-4.

## C. GASEOUS DISCHARGES

1. Ion Generation, Electron Energy Distributions, and Probe Measurements in a Low-Pressure Mercury Arc

Since the last report (Quarterly Progress Report, Oct. 15, 1956, p. 8), the study of the low-pressure mercury arc plasma has been completed. The results are available in the Ph.D. thesis of S. Aisenberg, Department of Physics, M.I.T., May 1957. A short summary of the experiments and the results will be given here.

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A series of Langmuir probe measurements was made on the plasma of a lowpressure mercury arc in order to obtain information about some of the fundamental processes in the plasma. This research showed that the actual ionization is many times larger than the direct ionization components, and that the effect of the electrondrift velocity on the direct ionization is negligible. The results of this research and the limited published information indicate that the metastable density is relatively independent of the electron density, at least at the higher pressures, and that the cumulative ionization is a linear function of the electron density and not a quadratic function. The effective cross section for ionization of the 6<sup>3</sup>P states was calculated to be at least 9.0 times greater than that for the ground state. The mobility of the electrons in the plasma was calculated, and it was found that the effective cross section for slow electrons in the plasma is essentially constant with an average value of  $42 \times 10^{-16}$  cm<sup>2</sup>. The ambipolar diffusion coefficient and the ambipolar mobility coefficient were determined as a function of  $E/p_0$  for an active plasma.

An original theory was developed (with the aid of Professor W. P. Allis) for ion mobility and diffusion in a strong nonuniform electric field. With the help of this theory, the mobility and longitudinal coefficients were calculated for mercury ions in the plasma. The radial electric field was calculated from the assumed Bessel-function electron-density distribution obtained from ambipolar-diffusion theory and from the Boltzmann potential and density-distribution relation. The effective cross section for mercury ions is found to increase from 31 to  $104 \times 10^{-16}$  cm<sup>2</sup> as the ion energy is increased from 0.44 to 1.37 ev. There is reasonable agreement with the limited data of others.

The theories and methods developed can be used for the measurement of ion cross section in other gases. A study was made of the collection of positive ions by a negative probe for comparison with theory, and a theory was developed for the ratio of saturation ion current to saturation electron current, which is in good agreement (approximately 3 per cent) with the experimental data. Several new experimental techniques were introduced. The partial pressures of the residual gases in the arc were in the range  $10^{-8}$  to  $10^{-7}$  mm Hg (or less). They were measured while the arc was in operation in the constant-temperature water bath. The probe potential was supplied by a low-impedance voltage source (featuring a high degree of negative feedback) which was specially designed for this experiment. A new method was developed to permit direct recording of the change of probe work-function as a function of time. This method involves the use of a constant-current source (to null the electron current to the probe, which was operated at a retarding potential) and an expanded-scale, high-input, impedance-recording millivoltmeter. This method should prove useful in future experiments.

S. Aisenberg

## D. EXPERIMENTAL TECHNIQUES

## 1. Spectral Emissivity of Tungsten

An experiment designed to measure the spectral emissivity of tungsten over the wavelength interval 310-800 m $\mu$  and the temperature interval 1600-2400°K has been summarized in the Quarterly Progress Reports of April 15, 1956, page 9; July 15, 1956, page 4; October 15, 1956, page 3; and April 15, 1957, page 7. The results of these measurements, for unpolarized light, with the tungsten surface viewed perpendicularly, are tabulated in Table I-1. The rms error of these measurements is 0.002 dimensionless (emissivity) units.

	Table I-1. Spectral Emissivity of Tungsten.							
Wavelength	Temperature							
(mµ)	1600°K	1800°K	2000°K	2200°K	2400°K			
300								
310	0.4798	0.4769	0.4740	0.4711	0.4682			
320	0.4823	0.4795	0.4767	0.4739	0.4711			
330	0.4828	0.4801	0.4774	0.4747	0.4720			
340	0,4823	0.4798	0.4773	0.4748	0.4723			
350	0.4816	0.4792	0.4768	0.4744	0.4720			
360	0.4804	0.4781	0.4758	0.4735	0.4712			
370	0.4791	0.4769	0.4747	0.4725	0,4703			
380	0.4775	0.4754	0.4733	0.4712	0.4691			
390	0.4754	0.4735	0.4716	0.4697	0.4678			
400	0.4735	0.4717	0.4699	0.4681	0.4663			
420	0.4694	0.4678	0.4662	0.4646	0.4630			
440	0.4651	0.4638	0.4625	0.4612	0.4599			
460	0.4620	0.4606	0.4592	0.4578	0,4564			
480	0.4595	0.4578	0.4561	0.4544	0.4527			
500	0,4571	0.4552	0.4533	0.4514	0.4495			
520	0.4553	0.4531	0.4509	0.4487	0.4465			
540	0.4539	0,4514	0.4489	0.4464	0.4439			
560	0.4522	0.4494	0.4466	0.4438	0.4410			
580	0.4501	0.4470	0.4439	0.4408	0.4377			
600	0.4477	0.4443	0.4409	0.4375	0.4341			
620	0.4450	0.4413	0.4376	0.4339	0.4302			
640	0.4428	0.4388	0.4348	0.4308	0.4268			
660	0.4412	0.4369	0.4326	0.4283	0.4240			
680	0,4400	0.4354	0,4308	0.4262	0.4216			
700	0.4375	0.4331	0.4287	0.4243	0.4199			
720	0.4340	0.4299	0.4258	0.4217	0.4176			
740	0.4304	0.4266	0.4228	0.4190	0.4152			
760	0.4274	0.4239	0.4204	0.4169	0.4134			
780	0.4246	0.4215	0,4184	0.4153	0.4122			
800	0,4222	0.4194	0.4166	0.4138	0,4110			

Equations for the variation in the spectral emissivity with the direction of polarization and the angle at which the surface was viewed were developed in terms of classical electromagnetic theory. In the Quarterly Progress Report of April 15, 1957, page 7, it was shown that this theory is in excellent agreement with the limited existing experimental data. We found that, by utilizing this theory, the basic optical properties of tungsten could be computed from an analysis of the emitted thermal radiation.

The index of refraction, N, is defined as the ratio of the phase velocity of light in vacuum to the phase velocity of light in tungsten. The extinction coefficient, K, measures the rate at which the intensity of the light is attenuated as it propagates through the tungsten structure according to the relation

Intensity =  $I_0 \exp(-4\pi K \frac{x}{\lambda_0})$ 

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where x is a coordinate that measures the distance that light has traveled through the tungsten structure;  $I_0$  is the light intensity at x = 0; and  $\lambda_0$  is the wavelength of the light if it were propagating in vacuum. The computed values of N and K are listed in Table I-2.

	Table I-2. Computed Values of N and K.							
A. Values of N								
Wavelength		Temperature						
(mµ)	1600°K	1800°K	2000°K	2200°K	2400°K			
350	4.136	4.084	4.040	3 994	3 950			
400	4.232	4.192	4.155	4 117	4 081			
450	4,291	4.255	4,224	4 194	4 168			
500	4.369	4.327	4.282	4 242	4 200			
550	4.443	4.392	4.337	4,280	4 221			
600	4.537	4.452	4.363	4 287	4 210			
665	4.613	4.508	4.396	4.286	4 186			
700	4.605	4.484	4.362	4.250	4.144			
B. Values of K								
Wavelength	Temperature							
(mµ)	1600°K	1800°K	2000°K	2200°K	2400°K			
350	2.824	2,865	2,904	2.945	2 988			
400	2.894	2,929	2,964	2,999	3.032			
450	3.004	3.034	3.062	3.085	3.110			
500	3.065	3.017	3.145	3.178	3.213			
550	3.099	3.155	3.203	3.256	3.304			
600	3.144	3,222	3,291	3.354	3.414			
665	3.215	3.308	3,401	3.484	3, 558			
700	3.269	3.367	3.457	3.540	3.607			

This report terminates the series of reports on this experiment. More details are given in a thesis, entitled "The Spectral Emissivity and Optical Constants of Tungsten," which was submitted to the Department of Physics, M.I.T., June 1957, in partial ful-fillment of the requirements for the degree of Doctor of Science, which will be published as Technical Report 328.

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